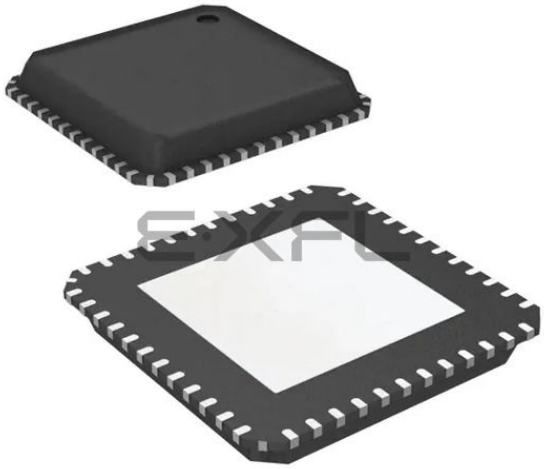
Infineon Technologies - XMC4100Q48F128BAXUMA1 Datasheet



Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, I²C, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I²S, LED, POR, PWM, WDT
Number of I/O	21
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	3.13V ~ 3.63V
Data Converters	A/D 9x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-VFQFN Exposed Pad
Supplier Device Package	PG-VQFN-48-71
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xmc4100q48f128baxuma1

About this Document

This Data Sheet is addressed to embedded hardware and software developers. It provides the reader with detailed descriptions about the ordering designations, available features, electrical and physical characteristics of the XMC4[12]00 series devices.

The document describes the characteristics of a superset of the XMC4[12]00 series devices. For simplicity, the various device types are referred to by the collective term XMC4[12]00 throughout this manual.

XMC4000 Family User Documentation

The set of user documentation includes:

- **Reference Manual**
  – decribes the functionality of the superset of devices.
- **Data Sheets**
  – list the complete ordering designations, available features and electrical characteristics of derivative devices.
- **Errata Sheets**
  – list deviations from the specifications given in the related Reference Manual or Data Sheets. Errata Sheets are provided for the superset of devices.

Attention: Please consult all parts of the documentation set to attain consolidated knowledge about your device.

Application related guidance is provided by **Users Guides** and **Application Notes**.

Please refer to **http://www.infineon.com/xmc4000** to get access to the latest versions of those documents.

1 Summary of Features

The XMC4[12]00 devices are members of the XMC4000 Family of microcontrollers based on the ARM Cortex-M4 processor core. The XMC4000 is a family of high performance and energy efficient microcontrollers optimized for Industrial Connectivity, Industrial Control, Power Conversion, Sense & Control.

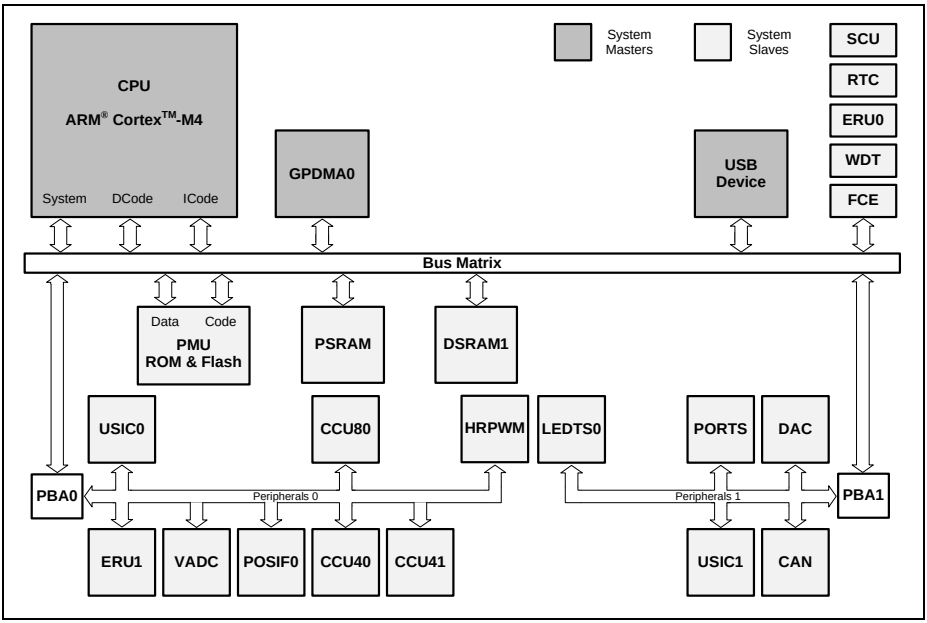


Figure 1 System Block Diagram

CPU Subsystem

- CPU Core
  - High Performance 32-bit ARM Cortex-M4 CPU
  - 16-bit and 32-bit Thumb2 instruction set
  - DSP/MAC instructions
  - System timer (SysTick) for Operating System support
- Floating Point Unit
- Memory Protection Unit
- Nested Vectored Interrupt Controller
- One General Purpose DMA with up-to 8 channels
- Event Request Unit (ERU) for programmable processing of external and internal service requests
- Flexible CRC Engine (FCE) for multiple bit error detection

1.3 Package Variants

Different markings of the XMC4[12]00 use different package variants. Details of those packages are given in the **Package Parameters** section of the Data Sheet.

Table 2 XMC4[12]00 Package Variants

Package Variant	Marking	Package
XMC4[12]00-F64	EES-AA, ES-AA, ES-AB, AB	PG-LQFP-64-19
XMC4[12]00-Q48		PG-VQFN-48-53
XMC4[12]00-F64	BA	PG-TQFP-64-19
XMC4[12]00-Q48		PG-VQFN-48-71

1.4 Device Type Features

The following table lists the available features per device type.

Table 3 Features of XMC4[12]00 Device Types

Derivative[1)]	LEDTS Intf.	USB Intf.	USIC Chan.	MultiCAN Nodes, MO
XMC4200-F64x256	1	1	2 x 2	N0, N1 MO[0..63]
XMC4200-Q48x256	1	1	2 x 2	N0, N1 MO[0..63]
XMC4100-F64x128	1	1	2 x 2	N0, N1 MO[0..63]
XMC4100-Q48x128	1	1	2 x 2	N0, N1 MO[0..63]
XMC4104-F64x64	1	–	2 x 2	–
XMC4104-Q48x64	1	–	2 x 2	–
XMC4104-F64x128	1	–	2 x 2	–
XMC4104-Q48x128	1	–	2 x 2	–
XMC4108-F64x64	–	–	2 x 2	N0, MO[0..31]
XMC4108-Q48x64	–	–	2 x 2	N0, MO[0..31]

1) x is a placeholder for the supported temperature range.

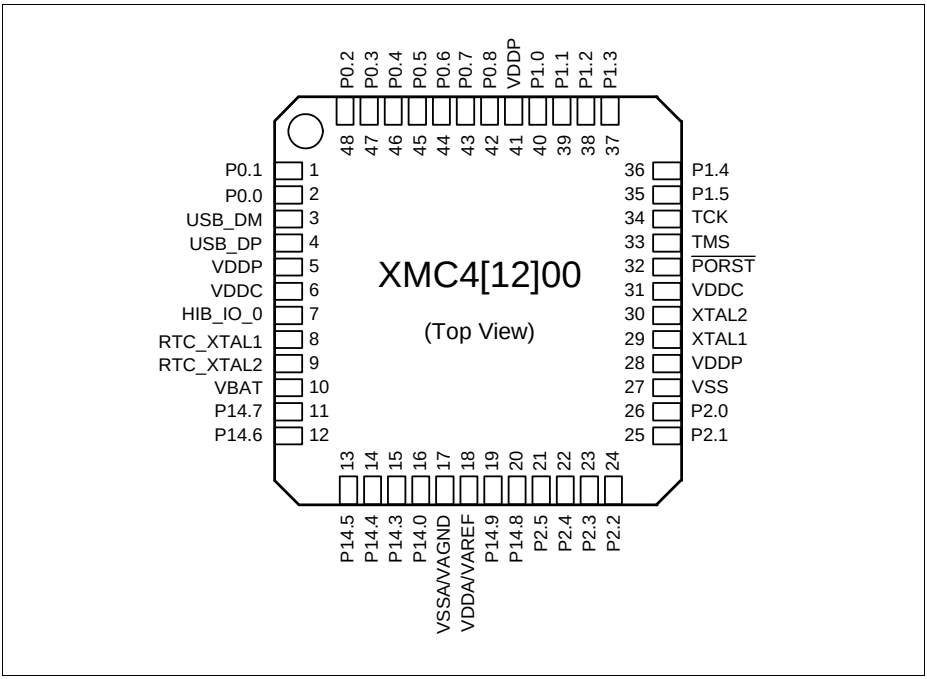


Figure 5 XMC4[12]00 PG-VQFN-48 Pin Configuration (top view)

Table 11 Package Pin Mapping (cont'd)

Function	LQFP-64 TQFP-64	VQFN-48	Pad Type	Notes
P0.11	59	-	A1+	
P1.0	52	40	A1+	
P1.1	51	39	A1+	
P1.2	50	38	A1+	
P1.3	49	37	A1+	
P1.4	48	36	A1+	
P1.5	47	35	A1+	
P1.7	55	-	A1+	
P1.8	54	-	A1+	
P1.9	53	-	A1+	
P1.15	46	-	A1+	
P2.0	34	26	A1+	
P2.1	33	25	A1+	After a system reset, via HWSEL this pin selects the DB.TDO function.
P2.2	32	24	A1+	
P2.3	31	23	A1+	
P2.4	30	22	A1+	
P2.5	29	21	A1+	
P2.6	36	-	A1+	
P2.7	35	-	A1+	
P2.8	28	-	A1+	
P2.9	27	-	A1+	
P2.14	26	-	A1+	
P2.15	25	-	A1+	
P3.0	5	-	A1+	
P14.0	20	16	AN/DIG_IN	
P14.3	19	15	AN/DIG_IN	
P14.4	18	14	AN/DIG_IN	
P14.5	17	13	AN/DIG_IN	
P14.6	16	12	AN/DIG_IN	
P14.7	15	11	AN/DIG_IN	
P14.8	24	20	AN/DAC/DIG_IN	

3 Electrical Parameters

3.1 General Parameters

3.1.1 Parameter Interpretation

The parameters listed in this section partly represent the characteristics of the XMC4[12]00 and partly its requirements on the system. To aid interpreting the parameters easily when evaluating them for a design, they are marked with an two-letter abbreviation in column “Symbol”:

- **CC**
  Such parameters indicate **C**ontroller **C**haracteristics, which are a distinctive feature of the XMC4[12]00 and must be regarded for system design.
- **SR**
  Such parameters indicate **S**ystem **R**equirements, which must be provided by the application system in which the XMC4[12]00 is designed in.

3.1.2 Absolute Maximum Ratings

Stresses above the values listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions may affect device reliability.

Table 14 Absolute Maximum Rating Parameters

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
Storage temperature	T_{ST}	SR	-65	–	150	°C	–
Junction temperature	T_J	SR	-40	–	150	°C	–
Voltage at 3.3 V power supply pins with respect to V_{SS}	V_{DDP}	SR	–	–	4.3	V	–
Voltage on any Class A and dedicated input pin with respect to V_{SS}	V_{IN}	SR	-1.0	–	V_{DDP} + 1.0 or max. 4.3	V	whichever is lower
Voltage on any analog input pin with respect to V_{AGND}	V_{AIN} V_{AREF}	SR	-1.0	–	V_{DDP} + 1.0 or max. 4.3	V	whichever is lower
Input current on any pin during overload condition	I_{IN}	SR	-10	–	+10	mA	
Absolute maximum sum of all input circuit currents for one port group during overload condition[1)]	ΣI_{IN}	SR	-25	–	+25	mA	
Absolute maximum sum of all input circuit currents during overload condition	ΣI_{IN}	SR	-100	–	+100	mA	

1) The port groups are defined in **Table 18**.

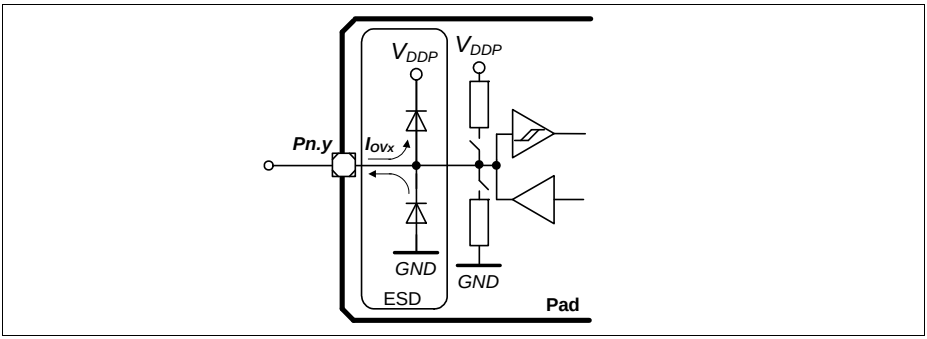


Figure 9 Input Overload Current via ESD structures

Table 16 and **Table 17** list input voltages that can be reached under overload conditions. Note that the absolute maximum input voltages as defined in the **Absolute Maximum Ratings** must not be exceeded during overload.

Table 16 PN-Junction Characterisitics for positive Overload

Pad Type	I_{OV} = 5 mA, T_J = -40 °C	I_{OV} = 5 mA, T_J = 150 °C
A1 / A1+	$V_{IN} = V_{DDP} + 1.0$ V	$V_{IN} = V_{DDP} + 0.75$ V
AN/DIG_IN	$V_{IN} = V_{DDP} + 1.0$ V	$V_{IN} = V_{DDP} + 0.75$ V

Table 17 PN-Junction Characterisitics for negative Overload

Pad Type	I_{OV} = 5 mA, T_J = -40 °C	I_{OV} = 5 mA, T_J = 150 °C
A1 / A1+	$V_{IN} = V_{SS} - 1.0$ V	$V_{IN} = V_{SS} - 0.75$ V
AN/DIG_IN	$V_{IN} = V_{DDP} - 1.0$ V	$V_{IN} = V_{DDP} - 0.75$ V

Table 18 Port Groups for Overload and Short-Circuit Current Sum Parameters

Group	Pins
1	P0.[12:0], P3.0
2	P14.[8:0]
3	P2.[15:0]
4	P1.[15:0]

3.2.2 Analog to Digital Converters (ADCx)

Table 25 ADC Parameters (Operating Conditions apply)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Analog reference voltage	V_{AREF} SR	–	–	–	V	$V_{AREF} = V_{DDA}$ shared analog supply and reference input pin
Alternate reference voltage[5]	V_{AREF} SR	V_{AGND} + 1	–	V_{DDA} + 0.05[1]	V	
Analog reference ground	V_{AGND} SR	–	–	–	V	$V_{AGND} = V_{SSA}$ shared analog supply and reference input pin
Alternate reference voltage range[2][5]	V_{AREF} - V_{AGND} SR	1	–	V_{DDA} + 0.1	V	
Analog input voltage	V_{AIN} SR	V_{AGND}	–	V_{DDA}	V	
Input leakage at analog inputs[3]	I_{OZ1} CC	-100	–	200	nA	$0.03 \times V_{DDA} < V_{AIN} < 0.97 \times V_{DDA}$
		-500	–	100	nA	$0\ V \le V_{AIN} \le 0.03 \times V_{DDA}$
		-100	–	500	nA	$0.97 \times V_{DDA} \le V_{AIN} \le V_{DDA}$
Internal ADC clock	f_{ADCI} CC	2	–	30	MHz	V_{DDA} = 3.3 V
Switched capacitance at the analog voltage inputs[4]	C_{AINSW} CC	–	4	6.5	pF	
Total capacitance of an analog input	C_{AINTOT} CC	–	12	20	pF	
Switched capacitance at the alternate reference voltage input[5][6]	C_{AREFSW} CC	–	15	30	pF	

9) The resulting current for a conversion can be calculated with $I_{AREF} = Q_{CONV} / t_c$.
The fastest 12-bit post-calibrated conversion of t_c = 566 ns results in a typical average current of I_{AREF} = 53 µA.

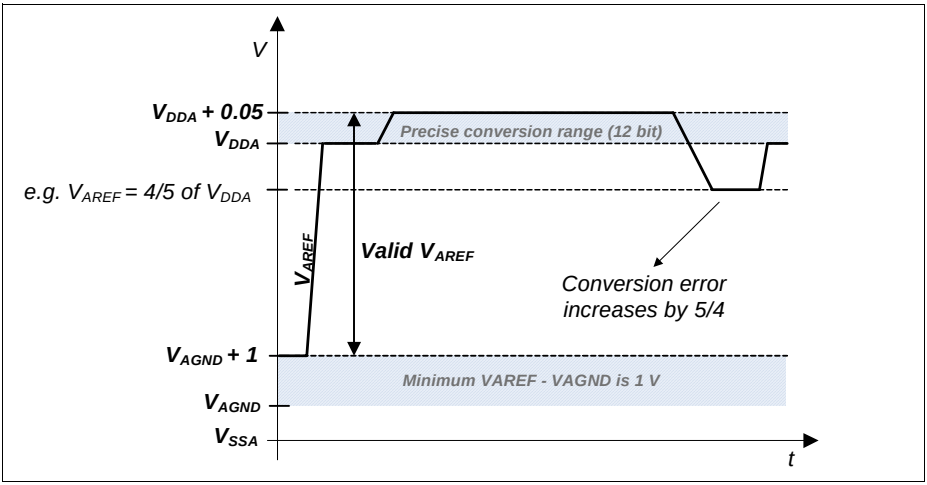


Figure 12 VADC Reference Voltage Range

Conversion Time

Table 26 Conversion Time (Operating Conditions apply)

Parameter	Symbol	Values	Unit	Note
Conversion time	t_C CC	$2 \times T_{ADC}$ + $(2 + N + STC + PC + DM) \times T_{ADCI}$	µs	N = 8, 10, 12 for N-bit conversion $T_{ADC} = 1 / f_{PERIPH}$ $T_{ADCI} = 1 / f_{ADCI}$

- STC defines additional clock cycles to extend the sample time
- PC adds two cycles if post-calibration is enabled
- DM adds one cycle for an extended conversion time of the MSB

Conversion Time Examples

System assumptions (max. f_{ADC}):
f_{ADC} = 80 MHz i.e. t_{ADC} = 12.5 ns, DIVA = 2, f_{ADCI} = 26.7 MHz i.e. t_{ADCI} = 37.5 ns
According to the given formulas the following minimum conversion times can be achieved (STC = 0, DM = 0):

12-bit post-calibrated conversion (PC = 2):
$t_{CN12C} = (2 + 12 + 2) \times t_{ADCI} + 2 \times t_{ADC} = 16 \times 37.5$ ns $+ 2 \times 12.5$ ns = 625 ns

12-bit uncalibrated conversion:
$t_{CN12} = (2 + 12) \times t_{ADCI} + 2 \times t_{ADC} = 14 \times 37.5$ ns $+ 2 \times 12.5$ ns = 550 ns

10-bit uncalibrated conversion:
$t_{CN10} = (2 + 10) \times t_{ADCI} + 2 \times t_{ADC} = 12 \times 37.5$ ns $+ 2 \times 12.5$ ns = 475 ns

8-bit uncalibrated:
$t_{CN8} = (2 + 8) \times t_{ADCI} + 2 \times t_{ADC} = 10 \times 37.5$ ns $+ 2 \times 12.5$ ns = 400 ns

System assumptions (max. f_{ADCI}):
f_{ADC} = 60 MHz i.e. t_{ADC} = 16.67 ns, DIVA = 1, f_{ADCI} = 30 MHz i.e. t_{ADCI} = 33.33 ns

12-bit post-calibrated conversion (PC = 2):
$t_{CN12C} = (2 + 12 + 2) \times t_{ADCI} + 2 \times t_{ADC} = 16 \times 33.33$ ns $+ 2 \times 16.67$ ns = 566 ns

3.2.4 Out-of-Range Comparator (ORC)

The Out-of-Range Comparator (ORC) triggers on analog input voltages (V_{AIN}) above the analog reference[1] (V_{AREF}) on selected input pins (GxORCy) and generates a service request trigger (GxORCOUTy).

Note: These parameters are not subject to production test, but verified by design and/or characterization.

The parameters in **Table 28** apply for the maximum reference voltage $V_{AREF} = V_{DDA} + 50$ mV.

Table 28 ORC Parameters (Operating Conditions apply)

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
DC Switching Level	V_{ODC}	CC	100	125	200	mV	Ax-marking devices $V_{AIN} \geq V_{AREF} + V_{ODC}$
Hysteresis	V_{OHYS}	CC	50	–	V_{ODC}	mV	
Detection Delay of a persistent Overvoltage	t_{ODD}	CC	55	–	450	ns	Ax-marking devices $V_{AIN} \geq V_{AREF} + 200$ mV
			45	–	105	ns	$V_{AIN} \geq V_{AREF} + 400$ mV
Always detected Overvoltage Pulse	t_{OPDD}	CC	440	–	–	ns	Ax-marking devices $V_{AIN} \geq V_{AREF} + 200$ mV
			90	–	–	ns	$V_{AIN} \geq V_{AREF} + 400$ mV
Never detected Overvoltage Pulse	t_{OPDN}	CC	–	–	49	ns	Ax-marking devices $V_{AIN} \geq V_{AREF} + 200$ mV
			–	–	30	ns	$V_{AIN} \geq V_{AREF} + 400$ mV
Release Delay	t_{ORD}	CC	65	–	105	ns	$V_{AIN} \leq V_{AREF}$
Enable Delay	t_{OED}	CC	–	100	200	ns	

1) Always the standard VADC reference, alternate references do not apply to the ORC.

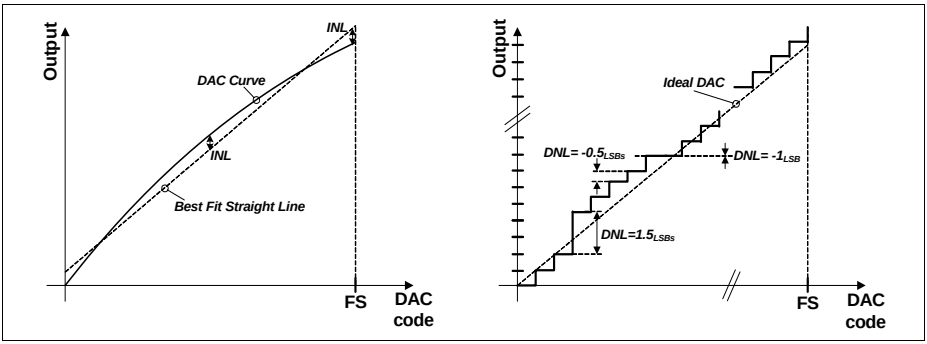


Figure 18 CSG DAC INL and DNL example

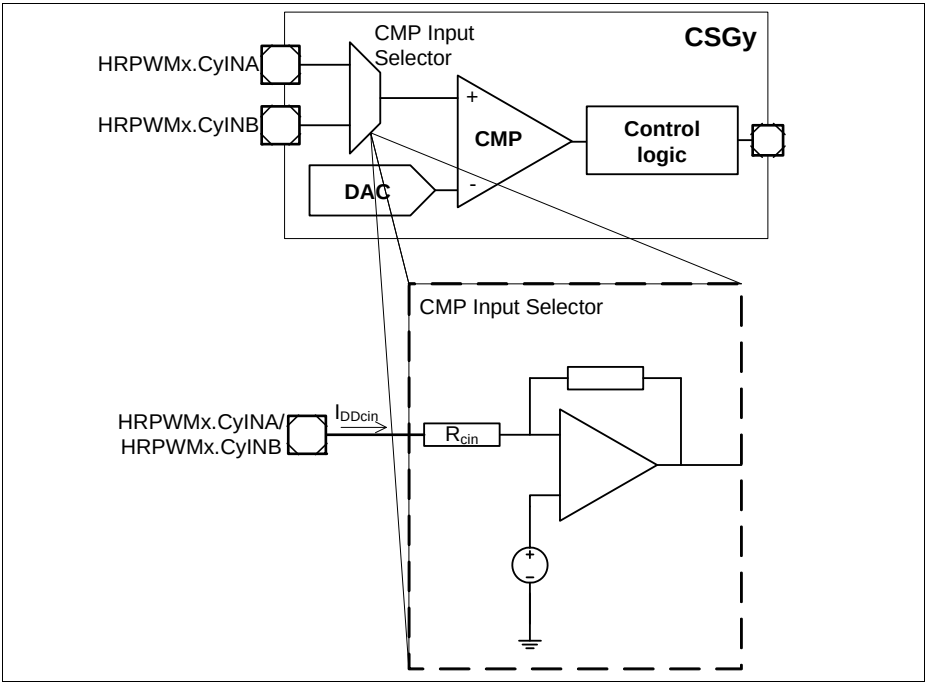


Figure 19 Input operation current

Table 37 RTC_XTAL Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input frequency	f_{OSC} SR	–	32.768	–	kHz	
Oscillator start-up time[1)2)3)]	t_{OSCS} CC	–	–	5	s	
Input voltage at RTC_XTAL1	V_{IX} SR	-0.3	–	V_{BAT} + 0.3	V	
Input amplitude (peak-to-peak) at RTC_XTAL1[2)4)]	V_{PPX} SR	0.4	–	–	V	
Input high voltage at RTC_XTAL1[5)]	V_{IHBX}SR	0.6 × V_{BAT}	–	V_{BAT} + 0.3	V	
Input low voltage at RTC_XTAL1[5)]	V_{ILBX} SR	-0.3	–	0.36 × V_{BAT}	V	
Input Hysteresis for RTC_XTAL1[5)6)]	V_{HYSX} CC	0.1 × V_{BAT}		–	V	3.0 V ≤ V_{BAT} < 3.6 V
		0.03 × V_{BAT}		–	V	V_{BAT} < 3.0 V
Input leakage current at RTC_XTAL1	I_{ILX1} CC	-100	–	100	nA	Oscillator power down 0 V ≤ V_{IX} ≤ V_{BAT}

1) t_{OSCS} is defined from the moment the oscillator is enabled by the user with SCU_OSCULCTRL.MODE until the oscillations reach an amplitude at RTC_XTAL1 of 400 mV.

2) The external oscillator circuitry must be optimized by the customer and checked for negative resistance and amplitude as recommended and specified by crystal suppliers.

3) For a reliable start of the oscillation in crystal mode it is required that $V_{BAT} \geq 3.0$ V. A running oscillation is maintained across the full V_{BAT} voltage range.

4) If the shaper unit is enabled and not bypassed.

5) If the shaper unit is bypassed, dedicated DC-thresholds have to be met.

6) Hysteresis is implemented to avoid metastable states and switching due to internal ground bounce. It can not be guaranteed that it suppresses switching due to external system noise.

Table 38 Power Supply Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Sleep supply current[3] Peripherals enabled Frequency: f_{CPU} / f_{PERIPH} / f_{CCU} in MHz	I_{DDPS} CC	–	76	–	mA	80 / 80 / 80
		–	73	–		80 / 40 / 40
		–	70	–		40 / 40 / 80
		–	56	–		24 / 24 / 24
		–	47	–		1 / 1 / 1
f_{CPU} / f_{PERIPH} / f_{CCU} in kHz		–	46	–		100 / 100 / 100
Sleep supply current[4] Peripherals disabled Frequency: f_{CPU} / f_{PERIPH} / f_{CCU} in MHz	I_{DDPS} CC	–	59	–	mA	80 / 80 / 80
		–	58	–		80 / 40 / 40
		–	57	–		40 / 40 / 80
		–	51	–		24 / 24 / 24
		–	46	–		1 / 1 / 1
f_{CPU} / f_{PERIPH} / f_{CCU} in kHz		–	46	–		100 / 100 / 100
Deep Sleep supply current[5] Flash in Sleep mode Frequency: f_{CPU} / f_{PERIPH} / f_{CCU} in MHz	I_{DDPD} CC	–	6.9	–	mA	24 / 24 / 24
		–	4.3	–		4 / 4 / 4
		–	3.8	–		1 / 1 / 1
f_{CPU} / f_{PERIPH} / f_{CCU} in kHz		–	4.5	–		100 / 100 / 100 [6]
Hibernate supply current RTC on[7]	I_{DDPH} CC	–	10.8	–	µA	V_{BAT} = 3.3 V
		–	8.0	–		V_{BAT} = 2.4 V
		–	6.8	–		V_{BAT} = 2.0 V
Hibernate supply current RTC off[8]	I_{DDPH} CC	–	10.3	–	µA	V_{BAT} = 3.3 V
		–	7.5	–		V_{BAT} = 2.4 V
		–	6.3	–		V_{BAT} = 2.0 V
Worst case active supply current[9]	I_{DDPA} CC	–	–	140 [10]	mA	V_{DDP} = 3.6 V, T_J = 150 °C
V_{DDA} power supply current	I_{DDA} CC	–	–	–[11]	mA	
I_{DDP} current at $\overline{\text{PORST}}$ Low	I_{DDP_PORST} CC	–	–	24	mA	V_{DDP} = 3.6 V, T_J = 150 °C

Table 40 Flash Memory Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Data Retention Time, User Configuration Block (UCB)[3)4)]	t_{RTU} CC	20	–	–	years	Max. 4 erase/program cycles per UCB
Endurance on 64 Kbyte Physical Sector PS4	N_{EPS4} CC	10000	–	–	cycles	BA-marking devices only! Cycling distributed over life time[5)]

1) In case the Program Verify feature detects weak bits, these bits will be programmed once more. The reprogramming takes an additional time of 5.5 ms.

2) The following formula applies to the wait state configuration: FCON.WSPFLASH × (1 / f_{CPU}) ≥ t_a.

3) Storage and inactive time included.

4) Values given are valid for an average weighted junction temperature of T_J = 110°C.

5) Only valid with robust EEPROM emulation algorithm, equally cycling the logical sectors. For more details see the Reference Manual.

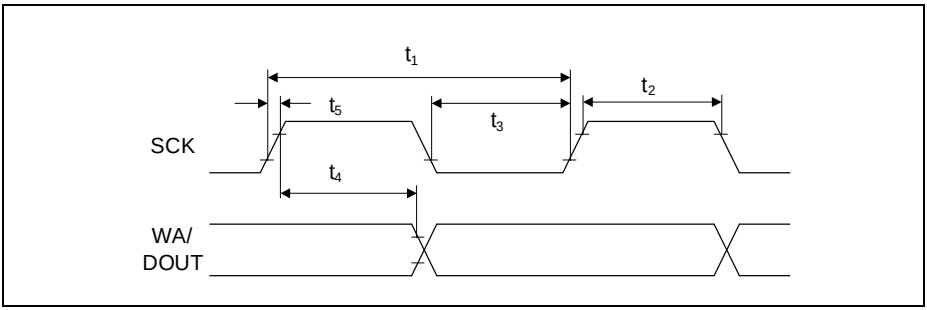


Figure 33 USIC IIS Master Transmitter Timing

Table 53 USIC IIS Slave Receiver Timing

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Clock period	t_6 SR	66.6	–	–	ns	
Clock high time	t_7 SR	0.35 x t_{6min}	–	–	ns	
Clock low time	t_8 SR	0.35 x t_{6min}	–	–	ns	
Set-up time	t_9 SR	0.2 x t_{6min}	–	–	ns	
Hold time	t_{10} SR	0	–	–	ns	

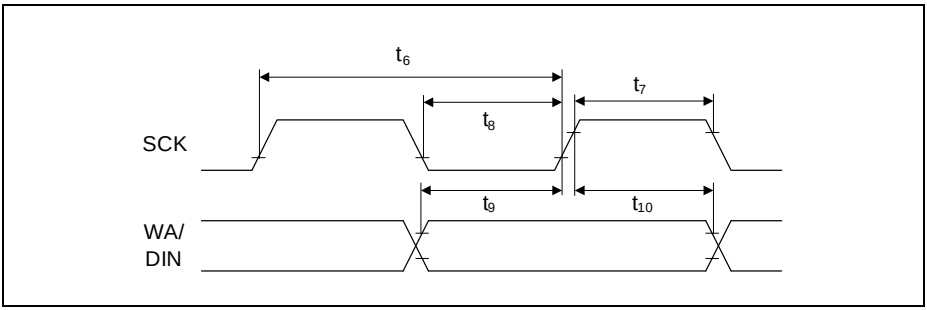


Figure 34 USIC IIS Slave Receiver Timing

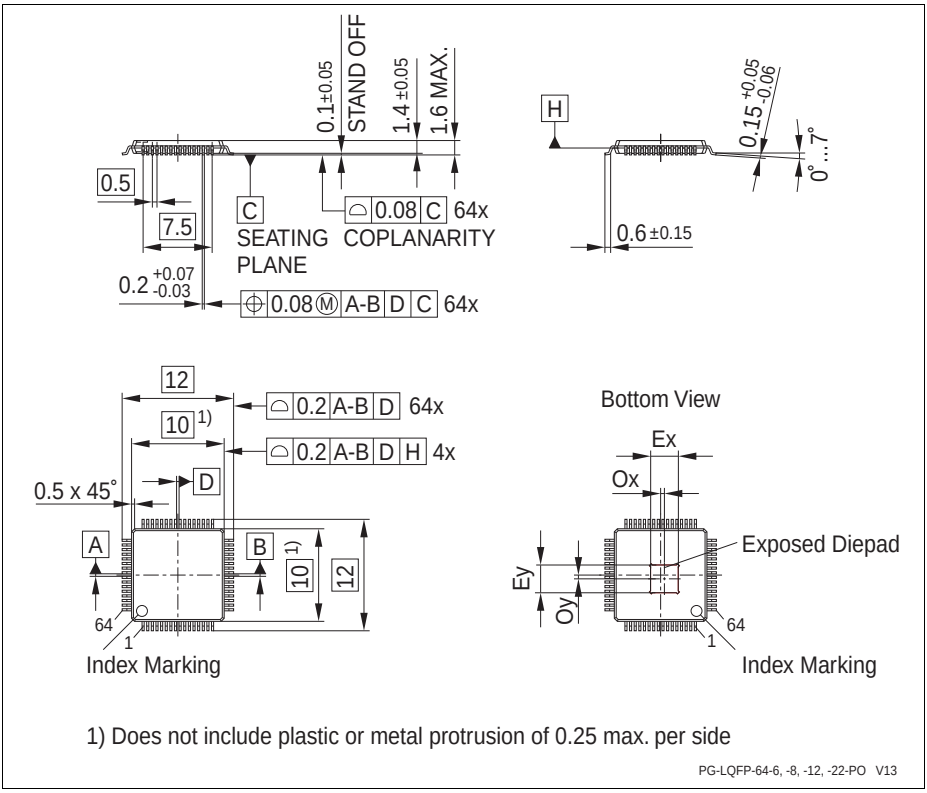


Figure 36 **PG-LQFP-64-19** (Plastic Green Low Profile Quad Flat Package)

w w w . i n f i n e o n . c o m

Published by Infineon Technologies AG